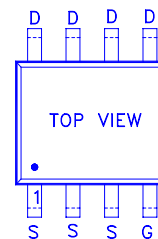
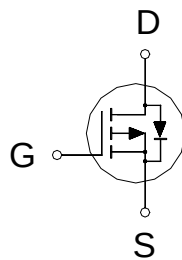


PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
-55V	80m Ω	-4.5A



4 :GATE
5,6,7,8 :DRAIN
1,2,3 :SOURCE

ABSOLUTE MAXIMUM RATINGS ($T_C = 25\text{ }^{\circ}\text{C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	-55	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current	$T_C = 25\text{ }^{\circ}\text{C}$	I_D	-4.5	A
	$T_C = 70\text{ }^{\circ}\text{C}$		-3.5	
Pulsed Drain Current ¹		I_{DM}	-20	
Power Dissipation	$T_C = 25\text{ }^{\circ}\text{C}$	P_D	2.5	W
	$T_C = 70\text{ }^{\circ}\text{C}$		1.3	
Operating Junction & Storage Temperature Range		T_j, T_{stg}	-55 to 150	$^{\circ}\text{C}$
Lead Temperature (¹ / ₁₆ " from case for 10 sec.)		T_L	275	

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient	$R_{\theta JA}$		50	$^{\circ}\text{C} / \text{W}$

¹Pulse width limited by maximum junction temperature.

²Duty cycle $\leq 1\%$

ELECTRICAL CHARACTERISTICS ($T_C = 25\text{ }^{\circ}\text{C}$, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-55			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-1	-1.5	-2.5	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 20V$			± 250	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -44V, V_{GS} = 0V$			1	μA
		$V_{DS} = -36V, V_{GS} = 0V, T_J = 125\text{ }^{\circ}C$			10	
On-State Drain Current ¹	$I_{D(ON)}$	$V_{DS} = -5V, V_{GS} = -10V$	-20			A
Drain-Source On-State Resistance ¹	$R_{DS(ON)}$	$V_{GS} = -4.5V, I_D = -3.5A$		90	150	m Ω
		$V_{GS} = -10V, I_D = -4.5A$		60	80	
Forward Transconductance ¹	g_{fs}	$V_{DS} = -10V, I_D = -4.5A$		9		S

DYNAMIC						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = -30V, f = 1MHz		760		pF
Output Capacitance	C _{oss}			90		
Reverse Transfer Capacitance	C _{rss}			40		
Total Gate Charge ²	Q _g	V _{DS} = 0.5V _{(BR)DSS} , V _{GS} = -10V, I _D = -4.5A		15		nC
Gate-Source Charge ²	Q _{gs}			2.5		
Gate-Drain Charge ²	Q _{gd}			3.0		
Turn-On Delay Time ²	t _{d(on)}	V _{DS} = -20V, I _D ≅ -1A, V _{GS} = -10V, R _{GS} = 6Ω		7	14	nS
Rise Time ²	t _r			10	20	
Turn-Off Delay Time ²	t _{d(off)}			19	34	
Fall Time ²	t _f			12	22	
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T _c = 25 °C)						
Continuous Current	I _S				-1.3	A
Pulsed Current ³	I _{SM}				-2.6	
Forward Voltage ¹	V _{SD}	I _F = I _S , V _{GS} = 0V			-1	V
Reverse Recovery Time	t _{rr}	I _F = -3.5 A, dI _F /dt = 100A / μS		15.5		nS
Reverse Recovery Charge	Q _{rr}			7.9		nC

¹Pulse test : Pulse Width $\leq 300 \mu sec$, Duty Cycle $\leq 2\%$.

²Independent of operating temperature.

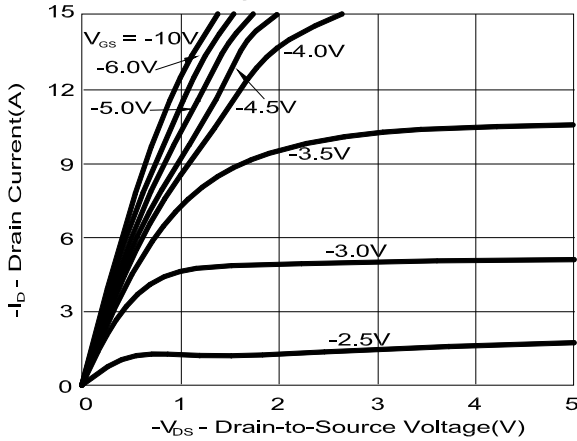
³Pulse width limited by maximum junction temperature.

REMARK: THE PRODUCT MARKED WITH "P8006EVG", DATE CODE or LOT #

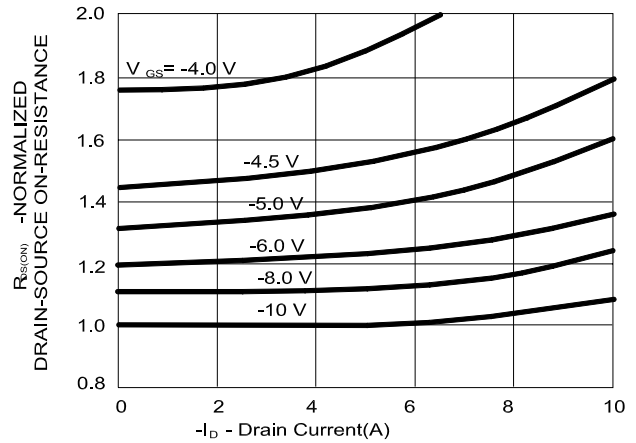
Orders for parts with Lead-Free plating can be placed using the PXXXXXXG parts name.

TYPICAL PERFORMANCE CHARACTERISTICS

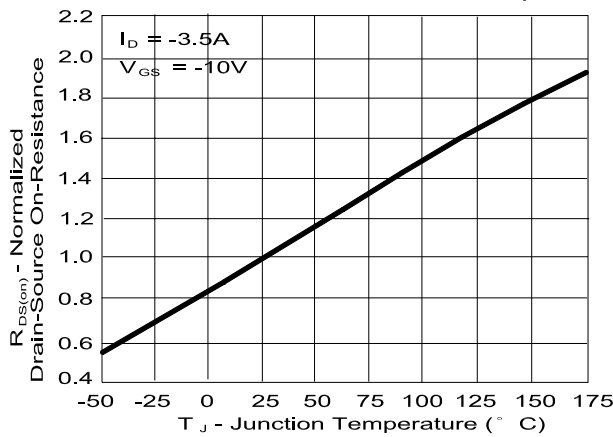
On-Region Characteristics



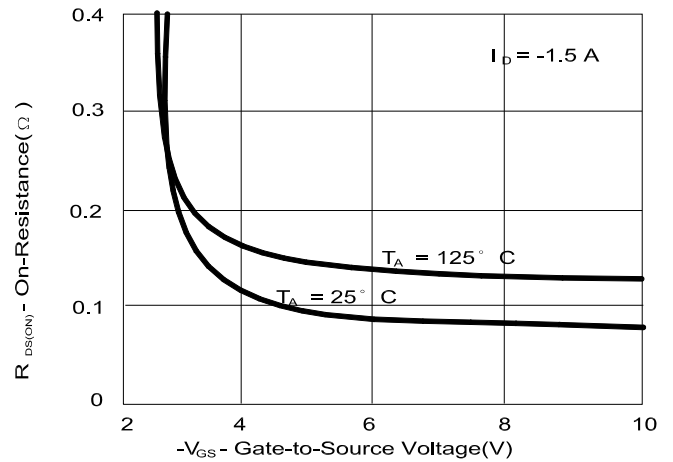
On-Resistance Variation with Drain Current and Gate Voltage



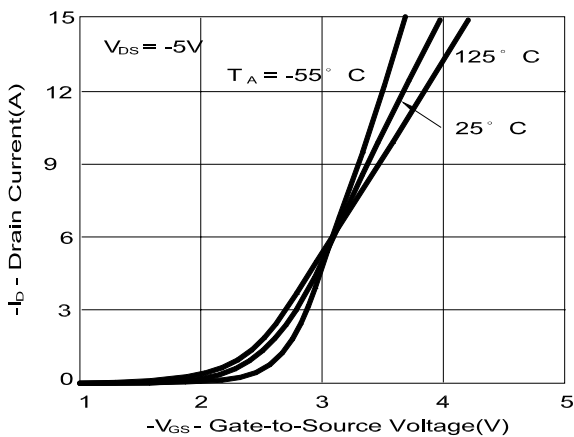
On-Resistance Variation with Temperature



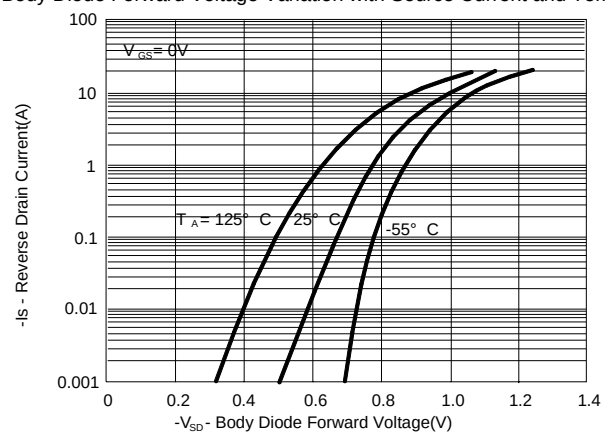
On-Resistance Variation with Gate-to-Source Voltage

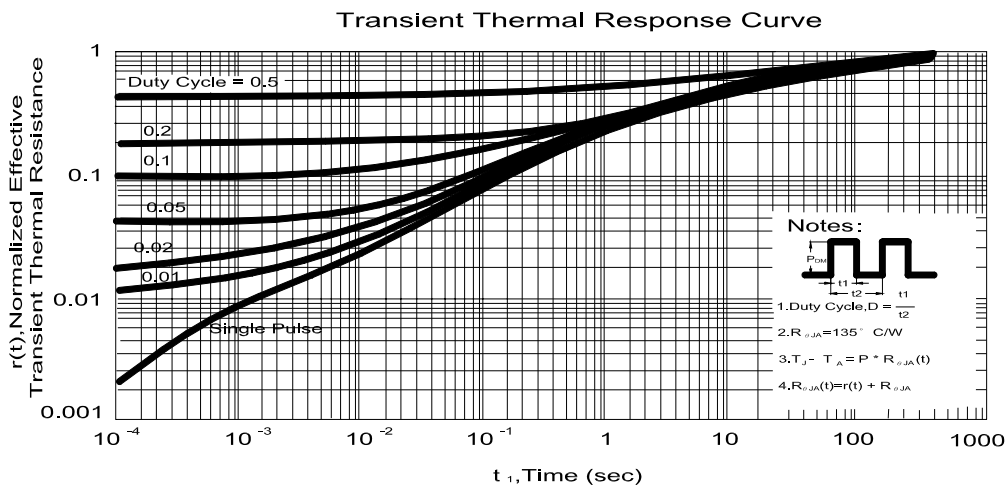
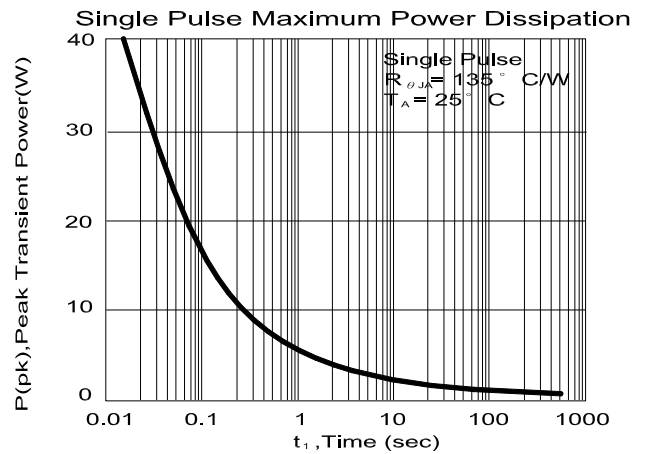
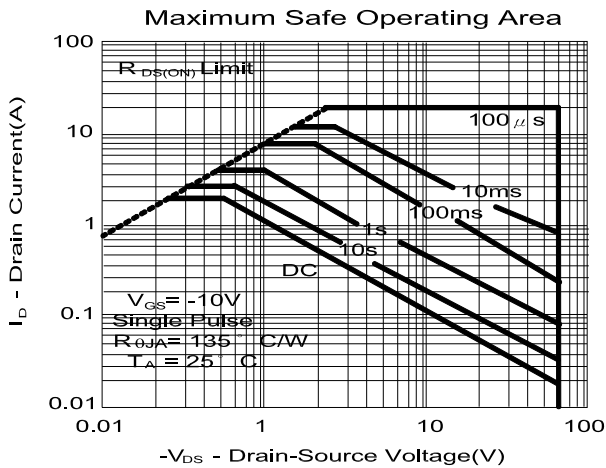
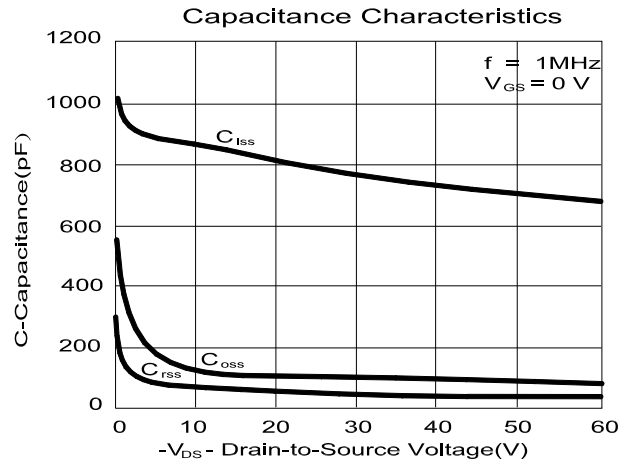
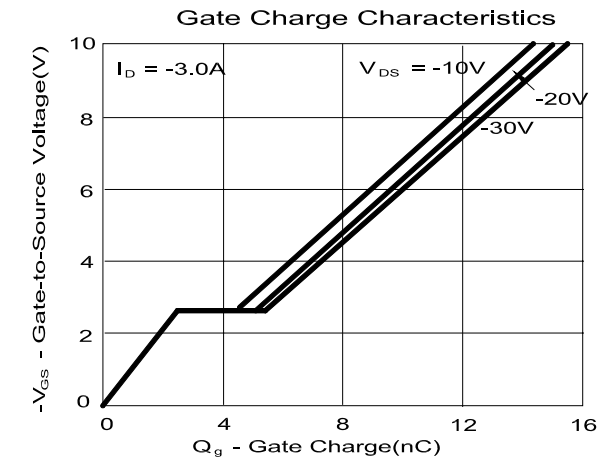


Transfer Characteristics



Body Diode Forward Voltage Variation with Source Current and Temperature





SOIC-8(D) MECHANICAL DATA

Dimension	mm			Dimension	mm		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	4.8	4.9	5.0	H	0.5	0.715	0.83
B	3.8	3.9	4.0	I	0.18	0.254	0.25
C	5.8	6.0	6.2	J		0.22	
D	0.38	0.445	0.51	K	0°	4°	8°
E		1.27		L			
F	1.35	1.55	1.75	M			
G	0.1	0.175	0.25	N			

